SONY

Ver.1.1

IMX335LQN

Diagonal 6.52 mm (Type 1/2.8) CMOS Solid-state Image Sensor with Square Pixel for Color Cameras

Description

The IMX335LQN is a diagonal 6.52 mm (Type 1/2.8) CMOS active pixel type solid-state image sensor with a square pixel array and 5.14 M effective pixels. This chip operates with analog 2.9 V, digital 1.2 V, and interface 1.8 V triple power supply, and has low power consumption. High sensitivity, low dark current and no smear are achieved through the adoption of R, G and B primary color mosaic filters. This chip features an electronic shutter with variable charge-integration time.

(Applications: Surveillance cameras, FA cameras, Industrial cameras)

Features

- ◆ CMOS active pixel type dots
- ◆ Built-in timing adjustment circuit, H/V driver and serial communication circuit
- ◆ Input frequency: 6 to 27 MHz / 37.125 MHz / 74.25 MHz
- ◆ Number of recommended recording pixels: 2592 (H) × 1944 (V) approx. 5.04 M pixels
- ◆ Readout mode

All-pixel scan mode

Horizontal/Vertical 2/2-line binning mode

Window cropping mode

Vertical / Horizontal direction-normal / inverted readout mode

◆ Readout rate

Maximum frame rate in All-pixel scan mode 2592 (H) × 1944 (V) A/D 10-bit : 60 frame/s

◆ High dynamic range (HDR) function

Multiple exposure HDR

Digital overlap HDR

- ◆ Variable-speed shutter function (resolution 1H units)
- ◆ 10-bit / 12-bit A/D converter
- ◆ CDS / PGA function

0 dB to 30 dB: Analog Gain 30 dB (step pitch 0.3 dB)

30.3 dB to 72 dB: Analog Gain 30 dB + Digital Gain 0.3 to 42 dB (step pitch 0.3 dB)

◆ Supports I/O

CSI-2 serial data output (2 Lane / 4 Lane, RAW10 / RAW12 output)

◆ Recommended exit pupil distance: -30 mm to -∞



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Device Structure

◆ CMOS image sensor

◆ Image size

◆ Total number of pixels

◆ Number of effective pixels

◆ Number of active pixels

◆ Number of recommended recording pixels

◆ Unit cell size

◆ Optical black

♦ Dummy

◆ Package

Type 1/2.8

2704 (H) × 2104 (V) approx. 5.69 M pixels

2616 (H) × 1964 (V) approx. 5.14 M pixels

2616 (H) × 1960 (V) approx. 5.11 M pixels

2592 (H) × 1944 (V) approx. 5.04 M pixels

 $2.0 \mu m (H) \times 2.0 \mu m (V)$

Horizontal (H) direction: Front 0 pixel, rear 0 pixel

Vertical (V) direction: Front 13 pixels, rear 0 pixel

Horizontal (H) direction: Front 0 pixel, rear 0 pixel

Vertical (V) direction: Front 0 pixel, rear 0 pixel

88 pin CSP BGA

Image Sensor Characteristics

(Tj = 60 °C)

ltem		Value	Remarks	
Sensitivity (F5.6)	Тур.	2200 Digit	1/30 s accumulation 12 bit converted value	
Saturation signal	Min.	3895 Digit	12 bit converted value	

Basic Drive Mode

Drive mode	Recommended number of recording pixels	Maximum frame rate [frame/s]	Output interface	ADC [bit]
All pixel	2592 (H) × 1944 (V) approx. 5.04 M pixels	60	CSI-2	10
Horizontal/ Vertical 2/2-line binning	1296 (H) × 972 (V) approx. 1.26 M pixels	60	CSI-2	10

